



Docket No.: M4065.0675/P675
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
John T. Moore, et al.

Application No.: 10/602,720

Confirmation No.: 9961

Filed: June 25, 2003

Art Unit: 2811

For: PCRAM CELL OPERATION METHOD TO
CONTROL ON/OFF RESISTANCE VARIATION

Examiner: Not Yet Assigned

**SUBMISSION OF RELEVANT INFORMATION INCLUDING
INFORMATION DISCLOSURE STATEMENT (IDS)**

Commissioner for Patents
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Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. 1.56, the attention of the U.S. Patent and Trademark Office is hereby directed to the documents listed below.

1. An Information Disclosure Statement, along with a reference citation form PTO SB/08 and the references cited in the form PTO SB/08.

2. A Declaration by Terry L. Gilton disclosing certain information previously disclosed in confidence to the assignee, Micron Technology, Inc. ("Micron") prior to the filing of the present application, but which is no longer subject to any confidentiality constraints between Micron and the disclosing party.

Dated: November 4, 2003

Respectfully submitted,

By 

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PTO/SB/08A (10-01)

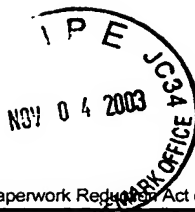
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<p>Substitute for form 1449A/PTO</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(use as many sheets as necessary)</p>				Complete if Known	
				Application Number	10/602,720
				Filing Date	June 25, 2003
				First Named Inventor	John T. Moore
				Art Unit	N/A
				Examiner Name	N/A
Sheet	1	of	11	Attorney Docket Number	M4065.0675/P675

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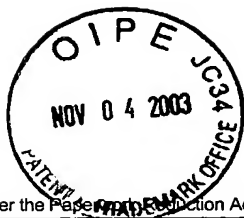
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
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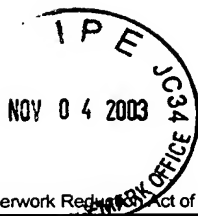
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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				Group Art Unit	N/A
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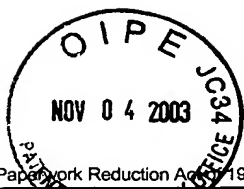
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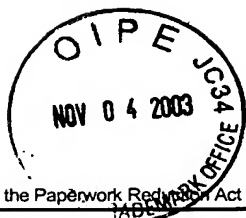
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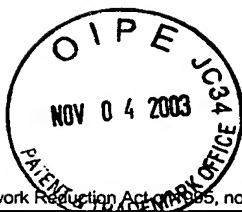
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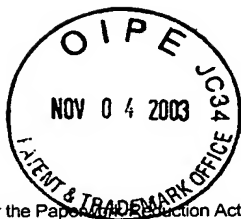
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Examiner Signature		Date Considered	
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